

NCE N-Channel Super Trench Power MOSFET

Description

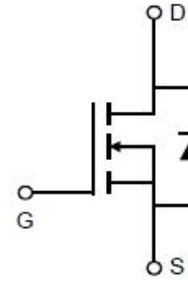
The NCEP30T17GU uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

- $V_{DS} = 30V, I_D = 170A$
 $R_{DS(ON)} = 0.97m\Omega$ (typical) @ $V_{GS} = 10V$
 $R_{DS(ON)} = 1.25m\Omega$ (typical) @ $V_{GS} = 4.5V$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

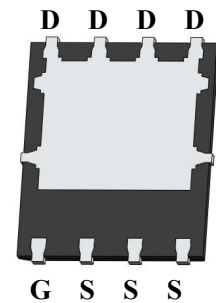
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification



Schematic Diagram



Top View



Bottom View

100% UIS TESTED!

100% ΔV_{ds} TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
P30T17GU	NCEP30T17GU	DFN5X6-8L	-	-	-

Absolute Maximum Ratings ($T_c = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous (Silicon Limited)	I_D	170	A
Drain Current-Continuous($T_c = 100^\circ C$)	$I_D(100^\circ C)$	125	A
Pulsed Drain Current	I_{DM}	680	A
Maximum Power Dissipation	P_D	135	W
Derating factor		1.08	W/ $^\circ C$
Single pulse avalanche energy ^(Note 1)	E_{AS}	1350	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.926	$^{\circ}\text{C/W}$
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Electrical Characteristics ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol		Condition	Min	Typ	Max	Unit
Off Characteristics							
Drain-Source Breakdown Voltage	BV _{DSS}		V _{GS} =0V I _D =250μA	30		-	V
Zero Gate Voltage Drain Current	I _{DSS}	T _J =25℃	V _{DS} =30V, V _{GS} =0V	-	-	1	μA
		T _J =55℃		-	-	1.5	μA
Gate-Body Leakage Current	I _{GSS}		V _{GS} =±5V, V _{DS} =0V	-	-	±80	nA
			V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics							
Gate Threshold Voltage	V _{GS(th)}		V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.0	V
Drain-Source On-State Resistance	R _{DS(ON)}		V _{GS} =10V, I _D =20A	0.75	0.97	1.2	mΩ
			V _{GS} =4.5V, I _D =20A	1	1.25	1.5	mΩ
Forward Transconductance	g _{FS}		V _{DS} =5V, I _D =20A		80	-	S
Dynamic Characteristics							
Input Capacitance	C _{iss}		V _{DS} =15V, V _{GS} =0V, F=1.0MHz	-	5300	6890	PF
Output Capacitance	C _{oss}			-	1800	2600	PF
Reverse Transfer Capacitance	C _{rss}			-	100	200	PF
Switching Characteristics							
Turn-on Delay Time ^(Note 2)	t _{d(on)}		V _{DD} =15V, I _D =20A V _{GS} =10V, R _G =1.6Ω	-	12	-	nS
Turn-on Rise Time ^(Note 2)	t _r			-	6.5	-	nS
Turn-Off Delay Time ^(Note 2)	t _{d(off)}			-	48	-	nS
Turn-Off Fall Time ^(Note 2)	t _f			-	7.5	-	nS
Total Gate Charge	Q _g		V _{DS} =15V, I _D =20A, V _{GS} =10V	-	90	126	nC
Gate-Source Charge	Q _{gs}			-	12	18	nC
Gate-Drain Charge	Q _{gd}			-	13	19.5	nC
Drain-Source Diode Characteristics							
Diode Forward Voltage	V _{SD}		V _{GS} =0V, I _S =20A	-	-	1.2	V
Diode Forward Current	I _S			-	-	170	A
Reverse Recovery Time	t _{rr}		T _J = 25℃, I _F = I _S	-	-	30	nS
Reverse Recovery Charge	Q _{rr}		di/dt = 100A/μs	-	-	110	nC

Notes:

1. E_{AS} condition : $T_J=25^{\circ}\text{C}, V_{DD}=20V, V_G=10V, L=0.5\text{mH}, R_g=25\Omega$
2. Guaranteed by design, not subject to production
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_J(\text{MAX})=150^{\circ}\text{C}$. The SOA curve provides a single pulse rating.

Typical Electrical and Thermal Characteristics

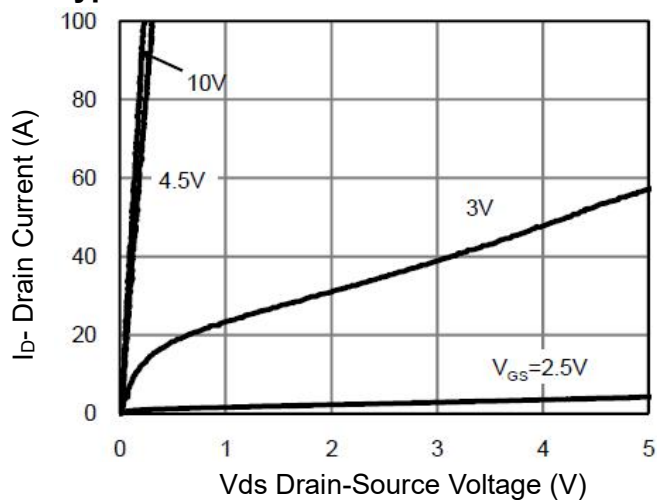


Figure 1 Output Characteristics

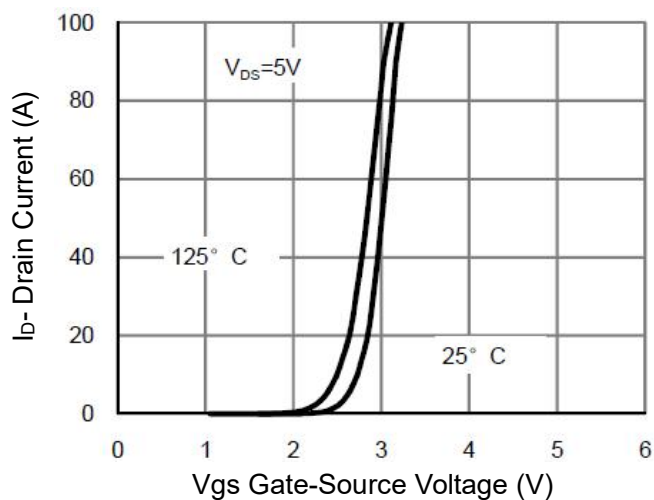


Figure 2 Transfer Characteristics

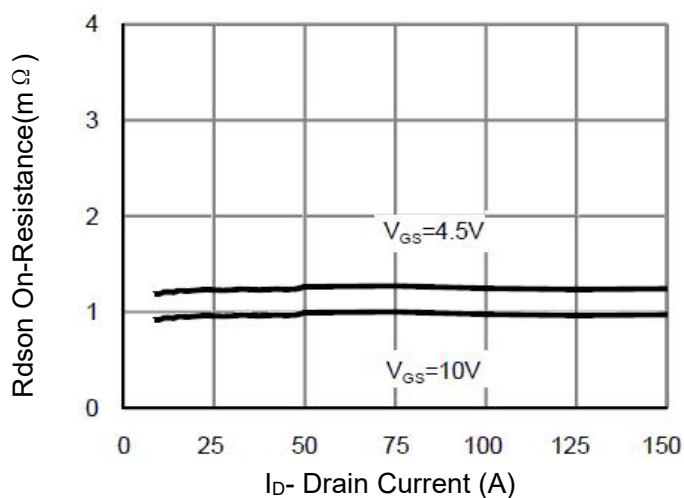


Figure 3 $R_{DS(on)}$ - Drain Current

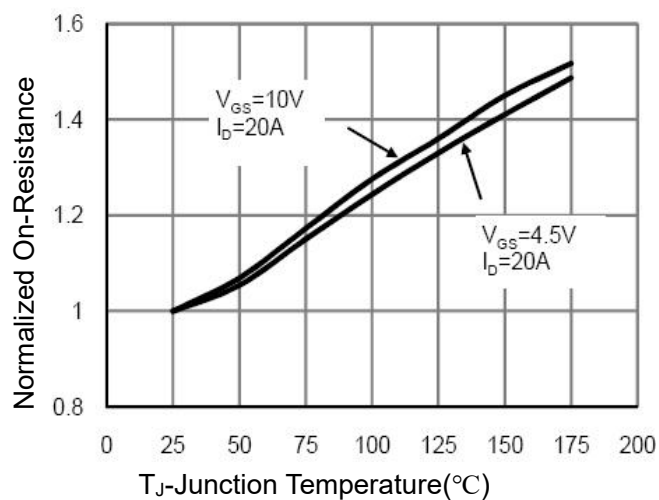


Figure 4 $R_{DS(on)}$ -Junction Temperature

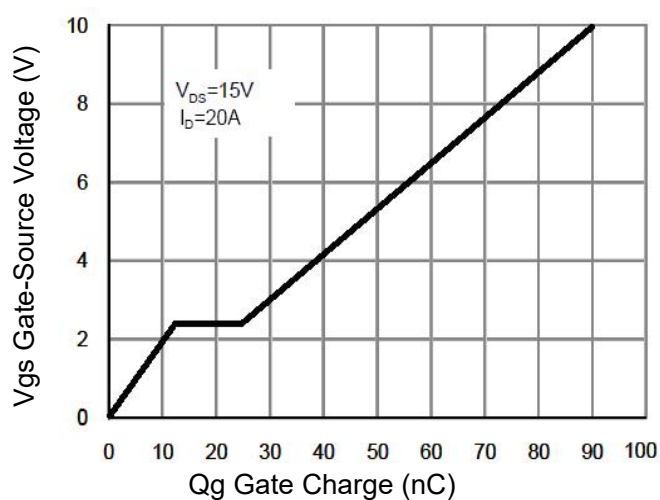


Figure 5 Gate Charge

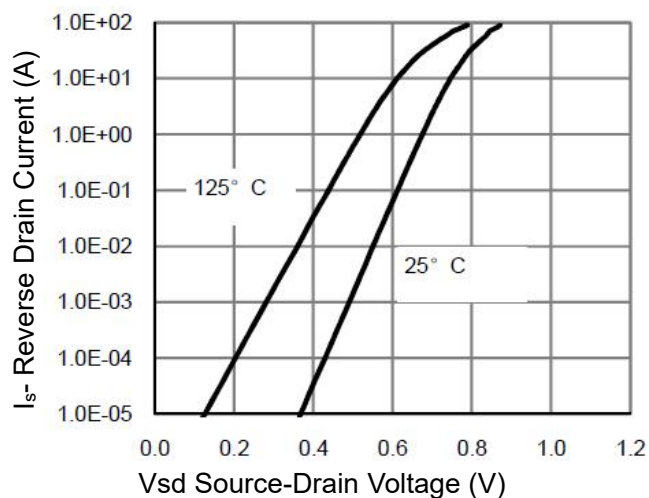


Figure 6 Source- Drain Diode Forward

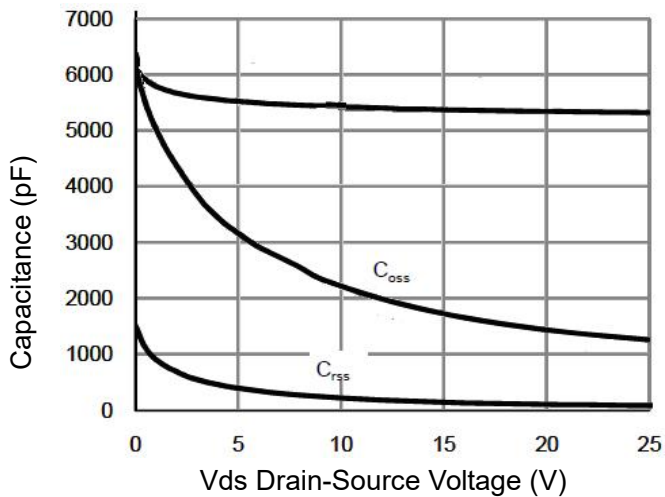


Figure 7 Capacitance vs Vds

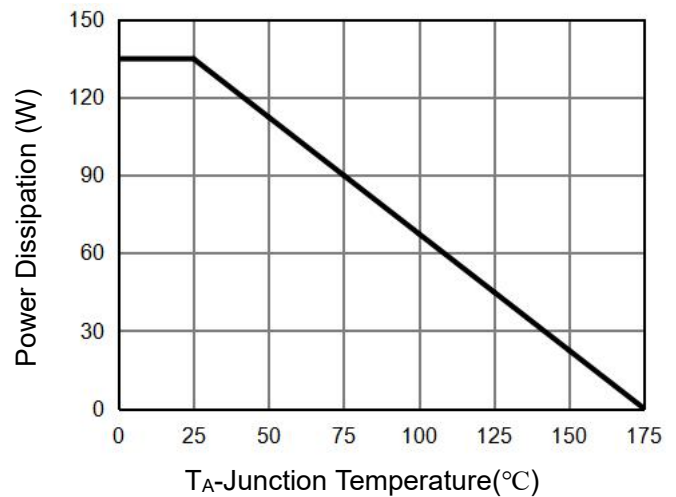


Figure 9 Power De-rating

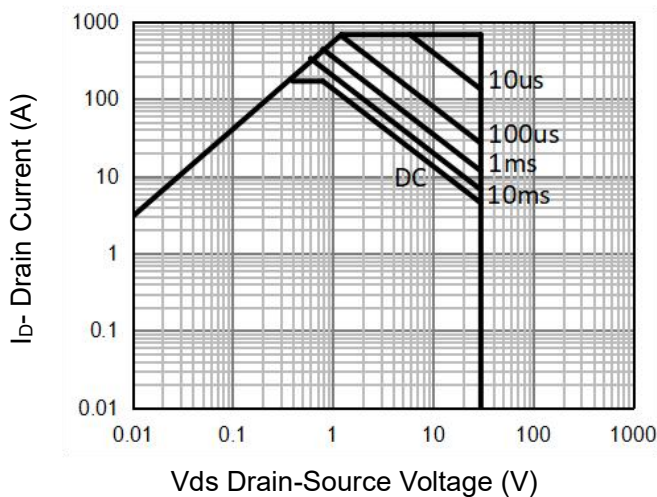


Figure 8 Safe Operation Area (Note3)

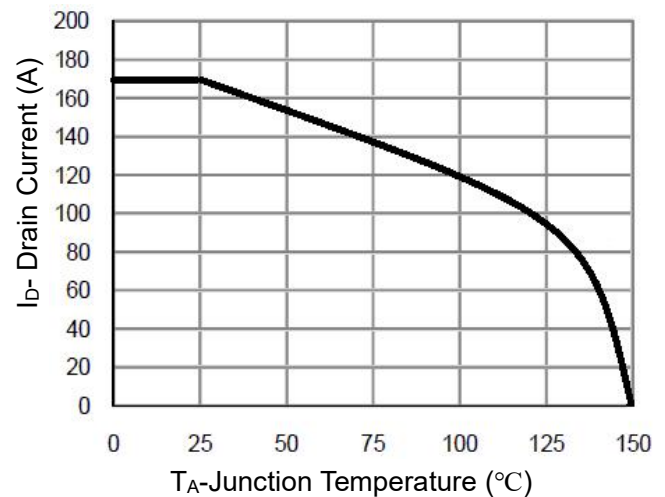


Figure 10 Current De-rating

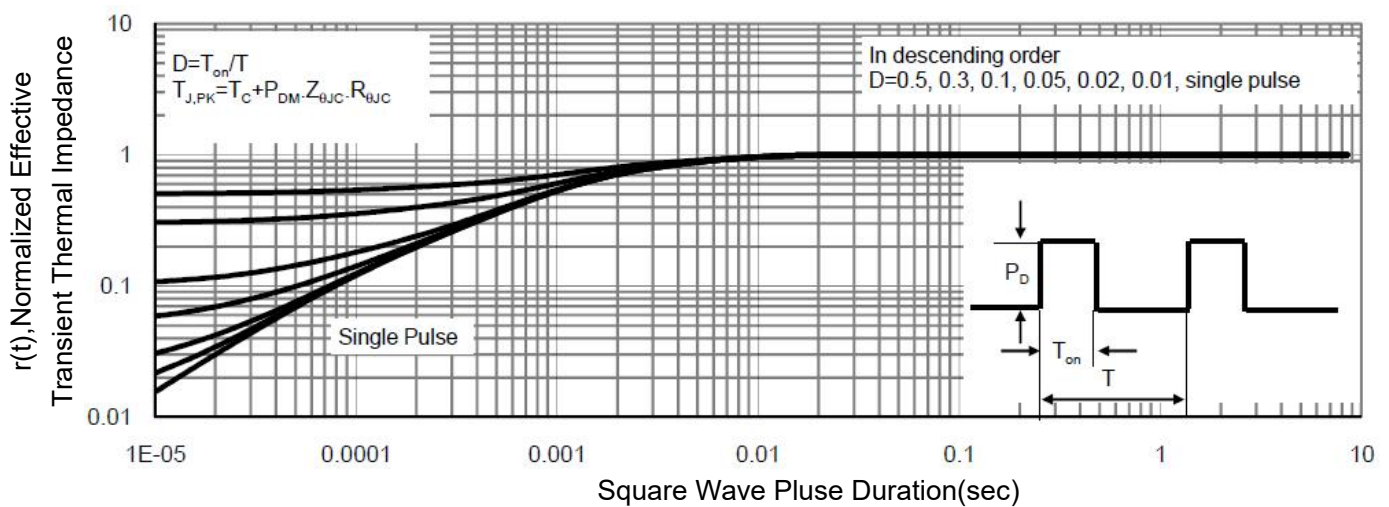
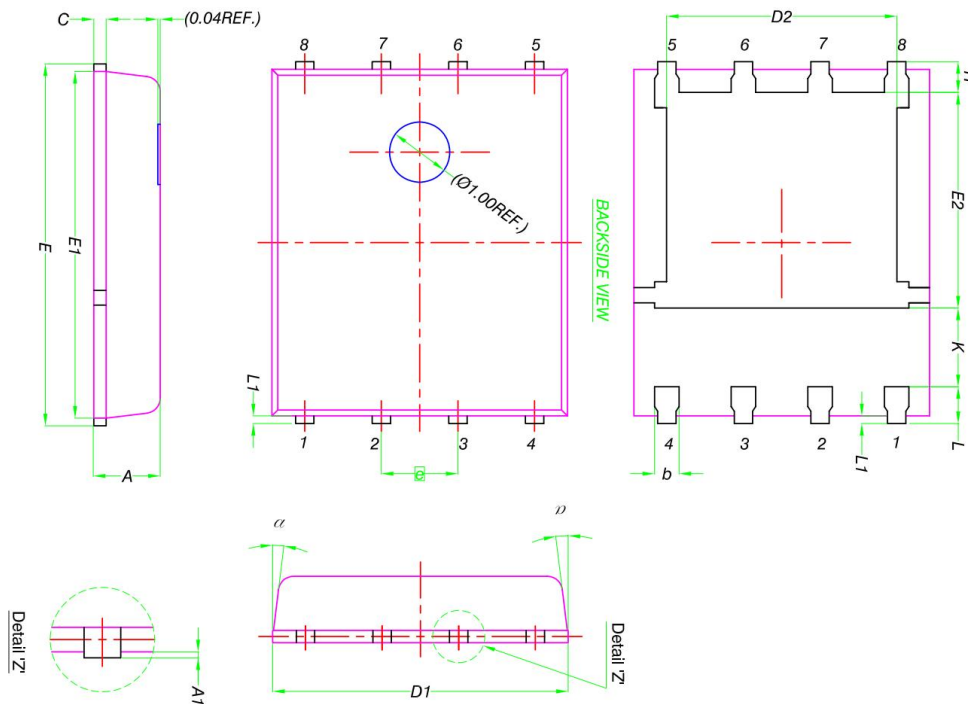
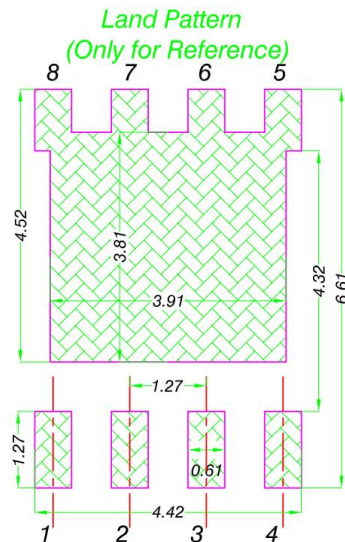


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN5X6-8L(G) Package Information



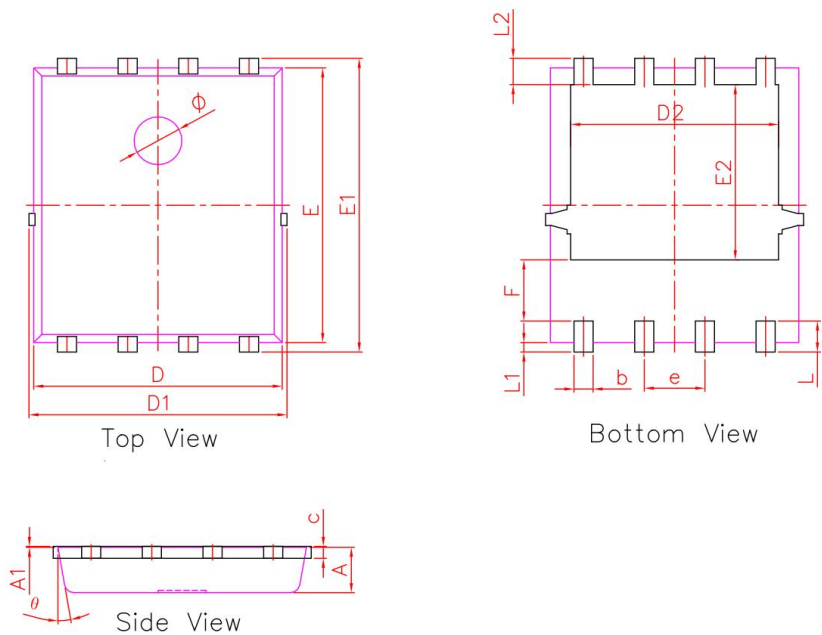
DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	0°	-	12°



Note:

1. All Dimension Are In mm.
2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs.
Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Tie Bar , Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
4. The Package Top May Be Smaller Than The Package Bottom.

DFN5X6-8L(E) Package Information



PDFN5X6-8L			
DIM.	MIN.	NOM.	MAX.
A	0.90	0.95	1.00
A1	0.00	0.02	0.05
b	0.35	0.40	0.50
c	0.20	0.25	0.30
D	5.10	5.20	5.30
D1	5.10	5.40	5.50
D2	4.25	4.35	4.45
e	1.27 BSC		
E	5.70	5.75	5.80
E1	6.00	6.15	6.30
E2	3.57	3.67	3.77
F	1.18	1.28	1.38
L	0.55	0.65	0.75
L1	0.15	0.20	0.25
L2	0.45	0.55	0.65
Φ	0.90	1.00	1.10
Θ	8°	10°	12°
All dimensions in millimeters			

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